



#### 55V 175°C N-CHANNEL ENHANCEMENT MODE MOSFET

#### **Product Summary**

BV <sub>DSS</sub>	R <sub>DS(ON)</sub> Max	I <sub>D</sub> Max T <sub>C</sub> = +25°C
55V	$12m\Omega @ V_{GS} = 10V$	80A
	$18m\Omega @ V_{GS} = 4.5V$	65A

### **Features**

- Rated to +175°C Ideal for High Ambient Temperature Environments
- 100% Unclamped Inductive Switching Ensures more Reliable and Robust End Application
- Low On-Resistance
- Low Input Capacitance
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Capable (Note 4)

### **Description and Applications**

This MOSFET is designed to meet the stringent requirements of Automotive applications. It is qualified to AEC-Q101, supported by a PPAP and is ideal for use in:

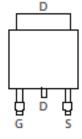
- Engine Management Systems
- Body Control Electronics
- DC/DC Converters

#### **Mechanical Data**

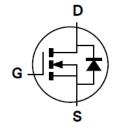
- Case: TO252 (DPAK)
- Case Material: Molded Plastic, "Green" Molding Compound.
   UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Finish Matte Tin Finish Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.33 grams (Approximate)



Top View



Pin Out Top View



**Equivalent Circuit** 

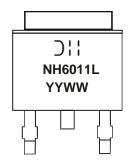
## **Ordering Information (Note 5)**

Part Number	Case	Packaging
DMNH6011LK3Q-13	TO252 (DPAK)	2,500/Tape & Reel

Notes: 1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.

- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. Automotive products are AEC-Q101 qualified and are PPAP capable. Refer to https://www.diodes.com/quality/.
- 5. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

### **Marking Information**



D!! =Manufacturer's Marking
NH6011L = Product Type Marking Code
YYWW = Date Code Marking
YY = Last Two Digits of Year (ex: 18= 2018)
WW = Week Code (01 to 53)

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## **Maximum Ratings** (@ $T_A = +25^{\circ}C$ , unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Drain-Source Voltage	V <sub>DSS</sub>	55	V	
Gate-Source Voltage		$V_{GSS}$	±12	V
Continuous Drain Current (Note 8), V <sub>GS</sub> = 10V	$T_{C} = +25^{\circ}C$ $T_{C} = +100^{\circ}C$	I <sub>D</sub>	80 50	А
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)	I <sub>DM</sub>	180	Α	
Maximum Continuous Body Diode Forward Current (Note 8)		I <sub>S</sub>	80	Α
Avalanche Current, L = 0.1mH (Note 9)		I <sub>AS</sub>	54	Α
Avalanche Energy, L = 0.1mH (Note 9)		Eas	147	mJ

#### Thermal Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Total Power Dissipation (Note 6)		$P_D$	1.6	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	$R_{\theta JA}$	80	°C/W
Total Power Dissipation (Note 7)		$P_D$	3.0	W
Thermal Resistance, Junction to Ambient (Note 7)	Steady State	$R_{\theta JA}$	42	°C/W
Thermal Resistance, Junction to Case (Note 8)		$R_{\theta JC}$	1.1	C/VV
Operating and Storage Temperature Range		T <sub>J,</sub> T <sub>STG</sub>	-55 to +175	°C

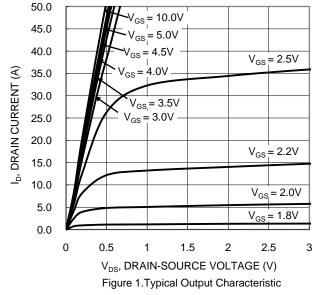
#### Electrical Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 10)				· ·	ı	1	
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	55	_	_	V	$V_{GS} = 0V, I_D = 250\mu A$	
Zero Gate Voltage Drain Current, T <sub>J</sub> = +25°C	I <sub>DSS</sub>	_	_	1	μΑ	V <sub>DS</sub> = 55V, V <sub>GS</sub> = 0V	
Gate-Source Leakage	I <sub>GSS</sub>	_	_	±100	nA	$V_{GS} = \pm 12V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 10)						•	
Gate Threshold Voltage	V <sub>GS(TH)</sub>	1	_	2	V	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	
Static Drain-Source On-Resistance	D	_	8.3	12	mΩ	$V_{GS} = 10V, I_D = 25A$	
Static Dialii-Source Off-Resistance	R <sub>DS(ON)</sub>	_	9.0	18	11152	V <sub>GS</sub> = 4.5V, I <sub>D</sub> = 25A	
Diode Forward Voltage	V <sub>SD</sub>	_	0.7	1.2	V	V <sub>GS</sub> = 0V, I <sub>S</sub> = 1.7A	
DYNAMIC CHARACTERISTICS (Note 11)			•		•	•	
Input Capacitance	C <sub>iss</sub>	_	3,077	_	pF	V 00V V 0V	
Output Capacitance	Coss	_	331	_	pF	$V_{DS} = 30V$ , $V_{GS} = 0V$ , $f = 1MHz$	
Reverse Transfer Capacitance	C <sub>rss</sub>	_	127	_	pF		
Gate Resistance	Rg	_	1.7	_	Ω	$V_{DS} = 0V$ , $V_{GS} = 0V$ , $f = 1MHz$	
Total Gate Charge (V <sub>GS</sub> = 4.5V)	Qg	_	23.4	_	nC		
Total Gate Charge (V <sub>GS</sub> = 10V)	Qg		49.1	_	nC	), 20V I 25A	
Gate-Source Charge	Q <sub>gs</sub>	_	5.3	_	nC	$V_{DS} = 30V, I_{D} = 25A$	
Gate-Drain Charge	Q <sub>gd</sub>	_	9.6	_	nC		
Turn-On Delay Time	t <sub>D(ON)</sub>	_	5.9	_	ns		
Turn-On Rise Time	t <sub>R</sub>	_	8.7	_	ns	$V_{GS} = 10V, V_{DS} = 30V,$	
Turn-Off Delay Time	t <sub>D(OFF)</sub>	_	28.2	_	ns	$R_G = 3\Omega, I_D = 25A$	
Turn-Off Fall Time	t <sub>F</sub>	_	10.2	_	ns	1	
Body Diode Reverse Recovery Time	t <sub>RR</sub>	_	30.1	_	ns	I <sub>F</sub> = 25A, di/dt = 100A/μs	
Body Diode Reverse Recovery Charge	Q <sub>RR</sub>	_	25.7	_	nC	I <sub>F</sub> = 25A, di/dt = 100A/μs	

- 6. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
- 7. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.
- 8. Thermal resistance from junction to soldering point (on the exposed drain pad).
- I<sub>AS</sub> and E<sub>AS</sub> ratings are based on low frequency and duty cycles to keep T<sub>J</sub> = +25°C.
   Short duration pulse test used to minimize self-heating effect.
   Guaranteed by design. Not subject to product testing.

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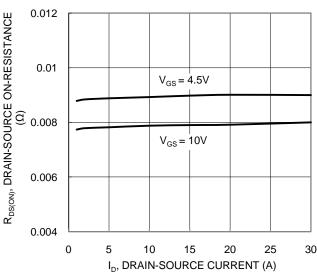


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

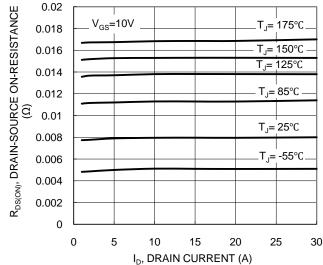
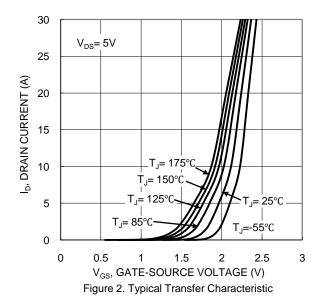
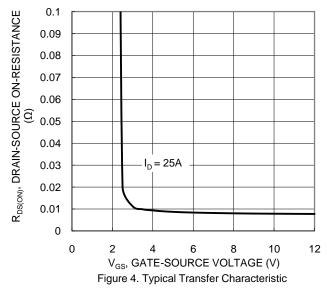


Figure 5. Typical On-Resistance vs. Drain Current and Temperature





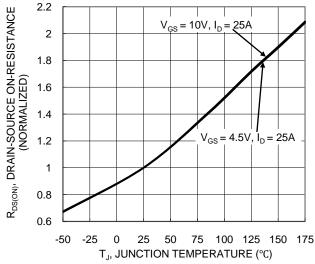
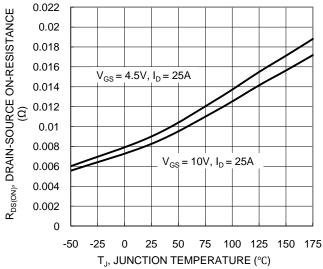
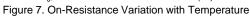
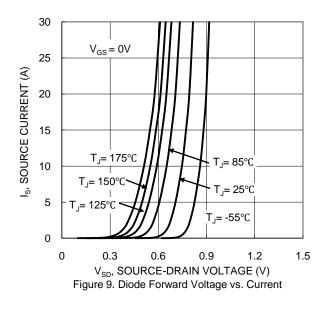


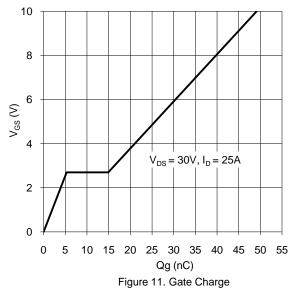
Figure 6. On-Resistance Variation with Temperature

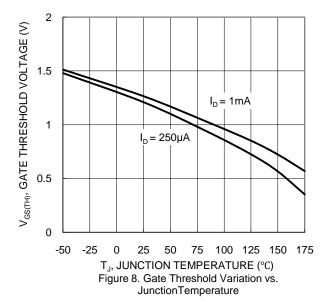


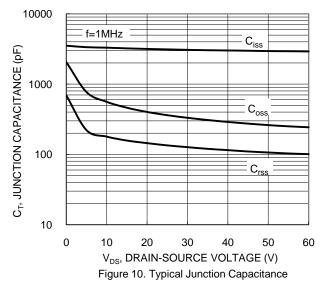


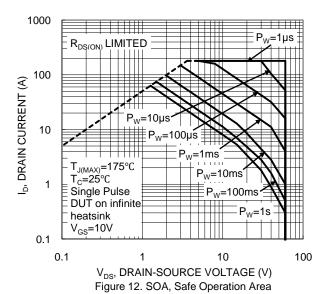














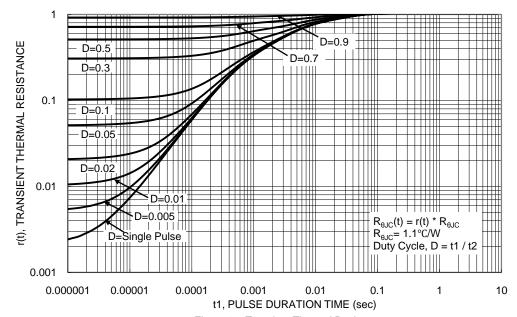
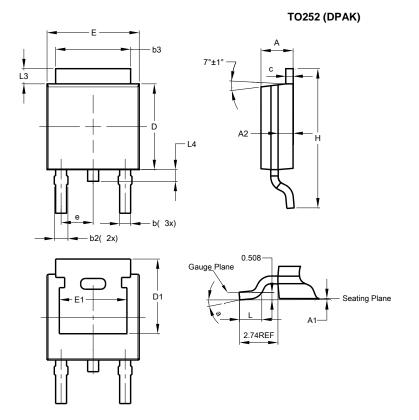


Figure 13. Transient Thermal Resistance



## **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.

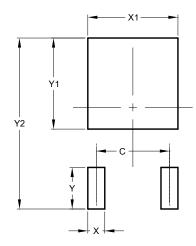


TO252 (DPAK)					
Dim	Min	Max	Тур		
Α	2.19	2.39	2.29		
A1	0.00	0.13	0.08		
A2	0.97	1.17	1.07		
b	0.64	0.88	0.783		
b2	0.76	1.14	0.95		
b3	5.21	5.46	5.33		
С	0.45	0.58	0.531		
D	6.00	6.20	6.10		
D1	5.21	-	-		
е	-	-	2.286		
Е	6.45	6.70	6.58		
E1	4.32	-	-		
Н	9.40	10.41	9.91		
L	1.40	1.78	1.59		
L3	0.88	1.27	1.08		
L4	0.64	1.02	0.83		
а	0°	10°	-		
All Dimensions in mm					

# **Suggested Pad Layout**

 $\label{prop:lease} Please see \ http://www.diodes.com/package-outlines.html for the latest version.$ 

#### TO252 (DPAK)



Dimensions	Value (in mm)		
С	4.572		
Х	1.060		
X1	5.632		
Υ	2.600		
Y1	5.700		
Y2	10.700		



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